

GATE TURN-OFF THYRISTOR

ATG675

Repetitive voltage up to **4500 V**
Mean on-state current **413 A**
Controllable on-state current **1000 A**
Surge on-state current **7 kA**

FINAL SPECIFICATION

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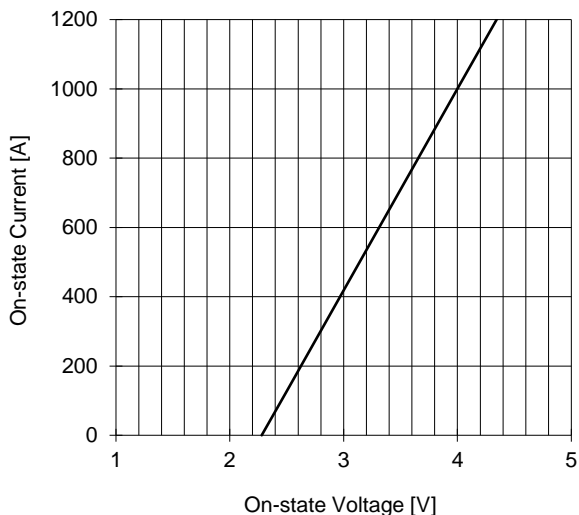
Symbol	Characteristic	Conditions	Tj °C	Value			Unit	
				min	typ	max		
BLOCKING								
V _{DRM}	Repetitive peak off-state voltage		125			4500	V	
V _{RRM}	Repetitive peak reverse voltage					17	V	
I _{DRM}	Repetitive peak off-state current	V _D =V _{DRM} R _{GK} <2 ohm				70	mA	
I _{RRM}	Repetitive peak reverse current	V _R =V _{RRM}				10	mA	
(dv/dt) _{crit}	Critical rate of rise of off-state voltage, min	Linear ramp up to 50% V _{DRM} , shorted G-K				1000	V/μS	
CONDUCTING								
I _{T(AV)}	Mean on-state current	180° sin, 50 Hz, Th=75°C, double side cooled				413	A	
I _{TSM}	Surge on-state current	sine wave, 10 ms, no reverse voltage	125			7	kA	
I ² t	I ² t for fusing coordination	10ms, no reverse voltage				245	A ² s10 ³	
V _T	On-state voltage	On-state current = 1000 A	125			4	V	
V _{T(TO)}	Threshold voltage		125			2,28	V	
r _T	On-state slope resistance					1,72	mohm	
SWITCHING ON								
t _{gt}	Gate controlled turn on time	I _T = 1000A; di/dt = 60A/μS	125			10	μS	
t _d	Delay time	I _{GM} = 20A						μS
E _{on}	Turn-on switching energy	V _D = 2250V						J
(di/dt) _{crit}	Critical rate of rise of on-state current	I _T = 1000A, I _{GM} = 60A, di _{GR} /dt = 35A/μS	125			400	A/μS	
SWITCHING OFF								
I _{TCM}	Controllable peak on-state current		125			1000	A	
t _{gq}	Gate controlled turn-off time	I _{TC} = I _{TCM} , V _{DM} = 2250V				19	μS	
t _s	Storage time	I _{GM} = 20 A di _{GR} /dt = 25A/μS						μS
E _{off}	Turn-off switching energy	L _S = 0,3 μH ; C _S = 1μF, R _S = 5 ohm						J
I _{RG}	Peak Turn-off reverse gate current						400	A
V _{DSP}	Spike voltage						900	V
TRIGGERING								
V _{GT}	Gate trigger voltage	V _D =24V	25			1,5	V	
I _{GT}	Gate trigger current		25			2,5	A	
V _{GRM}	Peak reverse gate voltage		25			17	V	
I _{GRM}	Peak reverse leakage gate current	V _{RG} = V _{RGM}	125			10	mA	
DISSIPATION								
R _{th(j-h)}	Thermal resistance junction to heatsink d.c.	Double side cooled				30	°C/kW	
T _{vj}	Virtual junction temperature					125	°C	
T _{stg}	Storage temperature			-40		150	°C	
MOUNTING								
W	Weight					530	g	
F	Mounting force			12.0	/	15.0	kN	
ORDERING INFORMATION : ATG675 S 45								
standard specification <input type="checkbox"/> <input type="checkbox"/> VDRM/1000								

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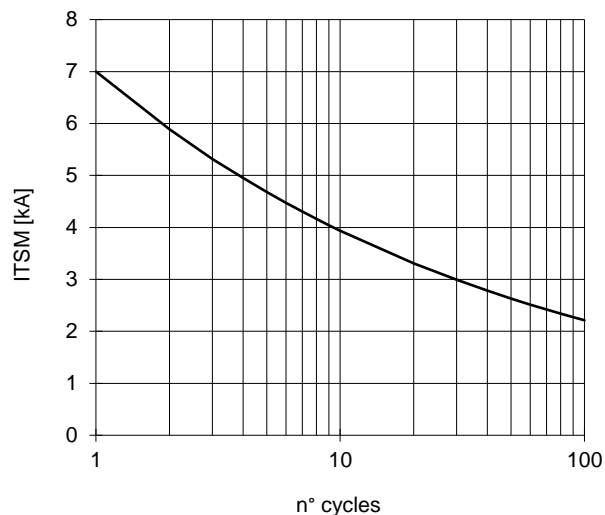


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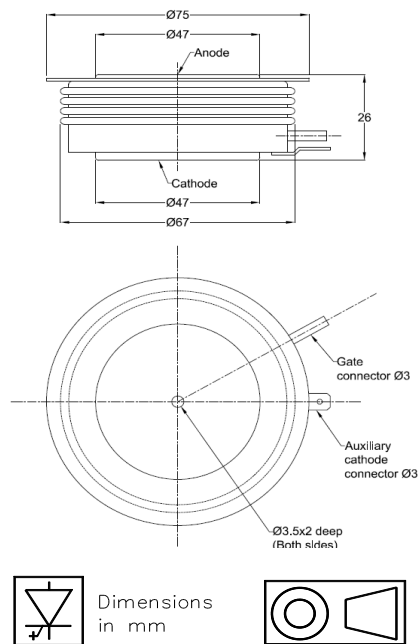
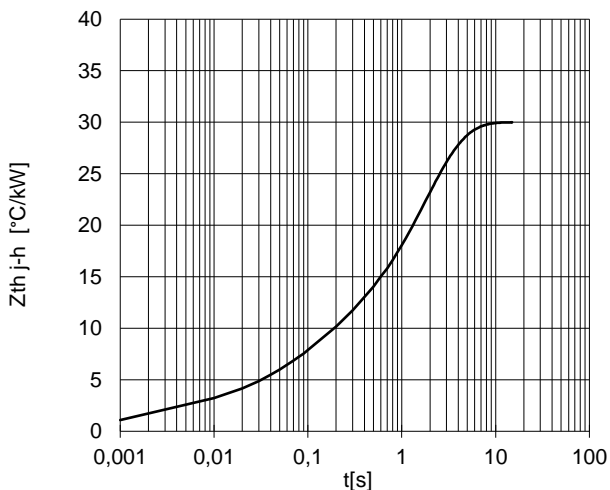
ON-STATE CHARACTERISTIC
T_j = 125 °C



SURGE CHARACTERISTIC
T_j = 125 °C



TRANSIENT THERMAL IMPEDANCE
DOUBLE SIDE COOLED



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All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness < .03 mm and roughness < 2 µm. In the interest of product improvement POSEICO Spa reserves the right to change any data given in this data sheet at any time without previous notice. If not stated otherwise the maximum value of ratings (symbols over shaded background) and characteristics is reported.

